

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
1	BRS	L1	0	amblard near gilles.in.	USPAT; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2004/02/0 6 16:40	
2	BRS	L2	2529	ler or edge near roughness	USPAT; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2004/02/0 6 16:40	
3	BRS	L3	4	(ler or edge near roughness) near25 (photo near resist or photo-resist)	USPAT; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2004/02/0 6 16:42	
4	BRS	L4	372	(ler or edge near roughness) near25 (resist)	USPAT; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2004/02/0 6 17:15	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
5	BRS	L5	58	(ler or edge near roughness) near25 (linewidth or line near width or line-width)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2004/02/0 6 17:24	
6	BRS	L6	3	(ler or edge near roughness) near25 (linewidth or line near width or line-width) near25 (mask)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2004/02/0 6 17:30	
7	BRS	L7	0	(photo) near20 (mask) near (ler)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2004/02/0 6 17:31	
8	BRS	L8	0	(photo) near20 (mask) near25 (ler)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2004/02/0 6 17:31	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
9	BRS	L9	0	(photo) near20 (mask) near25 ((ler) or (edge near roughness))	USPAT; US-P GPUB; EPO; JPO; DERW ENT; IBM TDB	2004/02/0 6 17:32	
10	BRS	L10	0	(photo) near20 (mask) near25 ((ler) or (edge near roughness))	USPAT; US-P GPUB; EPO; JPO; DERW ENT; IBM TDB	2004/02/0 6 17:32	
11	BRS	L11	2	(width) near20 (mask) near25 ((ler) or (edge near roughness))	USPAT; US-P GPUB; EPO; JPO; DERW ENT; IBM TDB	2004/02/0 6 17:33	
12	BRS	L12	95	(width) near25 ((ler) or (edge near roughness))	USPAT; US-P GPUB; EPO; JPO; DERW ENT; IBM TDB	2004/02/0 6 17:33	

	U	1	Document ID	Title	Current OR	Pages	Issue Date
1	<input type="checkbox"/>	<input type="checkbox"/>	US 20030219677 A1	Positive resist composition	430/270.1	12	20031127
2	<input type="checkbox"/>	<input type="checkbox"/>	US 20020182535 A1	Photoacid generator containing two kinds of sulfonium salt compound, chemically amplified resist containing the same and pattern transfer method	430/270.1	16	20021205
3	<input type="checkbox"/>	<input type="checkbox"/>	US 6638685 B2	Photoacid generator containing two kinds of sulfonium salt compound, chemically amplified resist containing the same and pattern transfer method	430/270.1	15	20031028
4	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 20030190069 A	Line edge roughness measurement method for micro objects, involves estimating deviation of edge with respect to scanning line and perpendicular to straight line, using edge coordinates		10	20031009